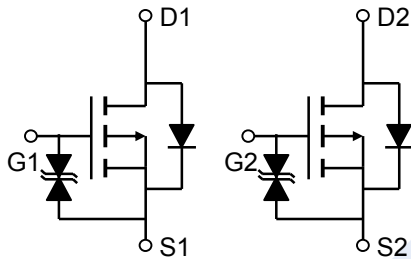
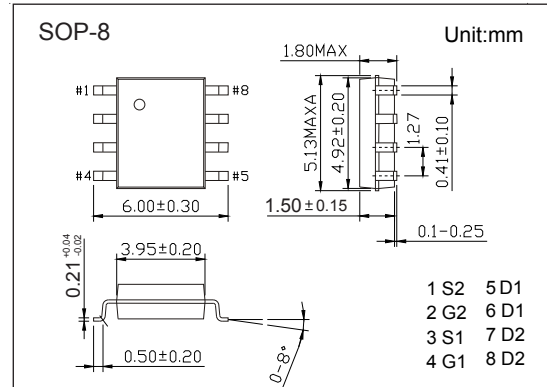


## Dual P-Channel MOSFET

### AO4815 (K04815)

#### ■ Features

- $V_{DS} (V) = -30V$
- $I_D = -8 A (V_{GS} = -20V)$
- $R_{DS(ON)} < 18m\Omega (V_{GS} = -20V)$
- $R_{DS(ON)} < 20m\Omega (V_{GS} = -10V)$
- ESD Rating: 2KV HBM



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DS}$	-30	V	
Gate-Source Voltage	$V_{GS}$	$\pm 25$		
Continuous Drain Current	$I_D$	$T_A=25^\circ C$	-8	A
		$T_A=70^\circ C$	-6.9	
Pulsed Drain Current	$I_{DM}$	-40		
Power Dissipation	$P_D$	$T_A=25^\circ C$	2	W
		$T_A=70^\circ C$	1.44	
Thermal Resistance.Junction- to-Ambient	$R_{thJA}$	$t \leq 10s$	62.5	$^\circ C/W$
		Steady-State	110	
Thermal Resistance.Junction- to-Lead	$R_{thJL}$	40		
Junction Temperature	$T_J$	150	$^\circ C$	
Storage Temperature Range	$T_{stg}$	-55 to 150		

## Dual P-Channel MOSFET

### AO4815 (K04815)

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =-250 μA, V <sub>GS</sub> =0V	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V			-1	μA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C			-5	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±25V			±1	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1		-3	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-20V, I <sub>D</sub> =-8A			18	mΩ
		V <sub>GS</sub> =-20V, I <sub>D</sub> =-8A, T <sub>J</sub> =125°C			24	
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-8A			20	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A		37		
On State Drain Current	I <sub>D(ON)</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-5V	-40			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-8A		15		S
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz		2330	2900	pF
Output Capacitance	C <sub>oss</sub>			480		
Reverse Transfer Capacitance	C <sub>rss</sub>			320		
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		6.8	10	Ω
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-8A		41	52	nC
Gate Source Charge	Q <sub>gs</sub>			10		
Gate Drain Charge	Q <sub>gd</sub>			12		
Turn-On DelayTime	t <sub>d(on)</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =1.8Ω, R <sub>GEN</sub> =3Ω		13		ns
Turn-On Rise Time	t <sub>r</sub>			12		
Turn-Off DelayTime	t <sub>d(off)</sub>			51		
Turn-Off Fall Time	t <sub>f</sub>			30.5		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-8A, di/dt= 100A/us		28	35	nC
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			20.5		
Maximum Body-Diode Continuous Current	I <sub>S</sub>				-2.6	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V			-1	V

Note. The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

#### ■ Marking

Marking	4815 KA****
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## Dual P-Channel MOSFET AO4815 (KO4815)

■ Typical Characteristics

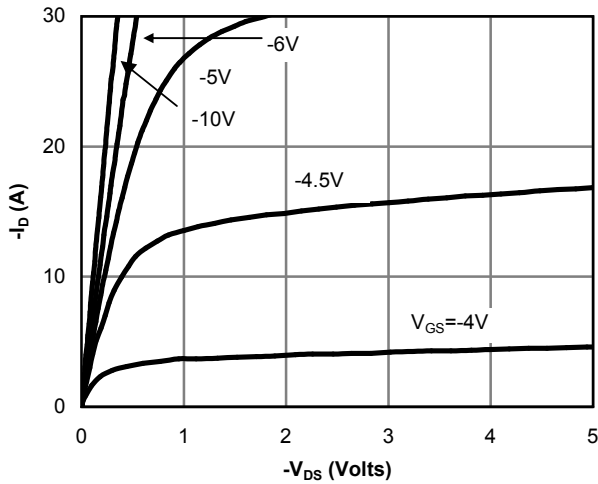


Figure 1: On-Region Characteristics

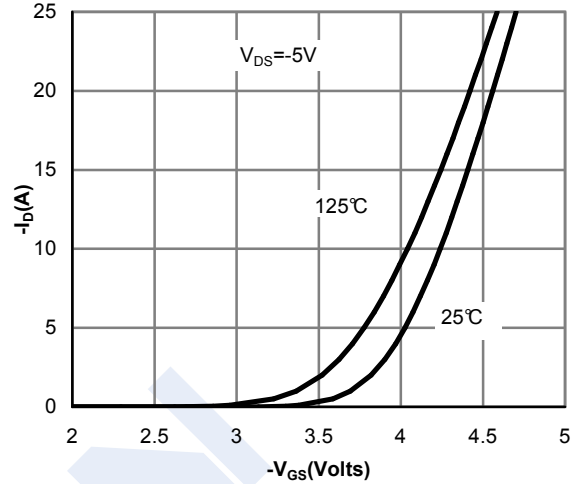


Figure 2: Transfer Characteristics

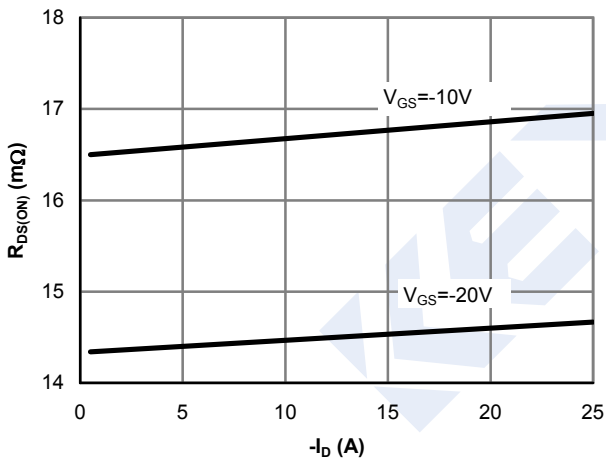


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

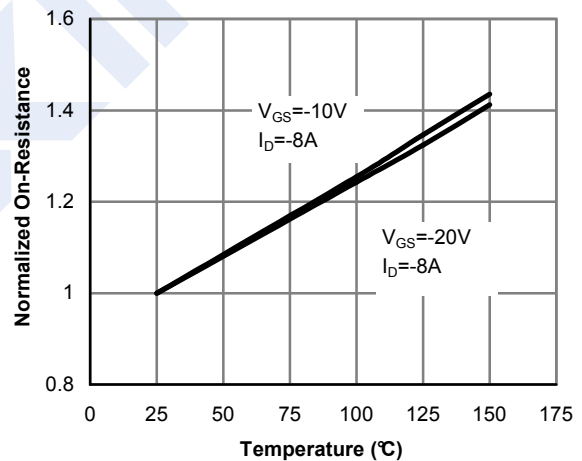


Figure 4: On-Resistance vs. Junction Temperature

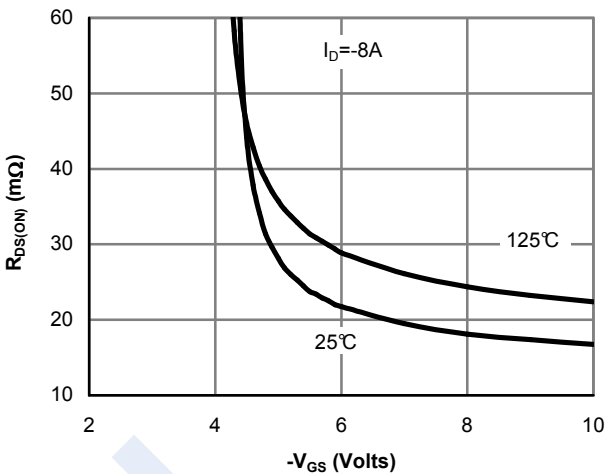


Figure 5: On-Resistance vs. Gate-Source Voltage

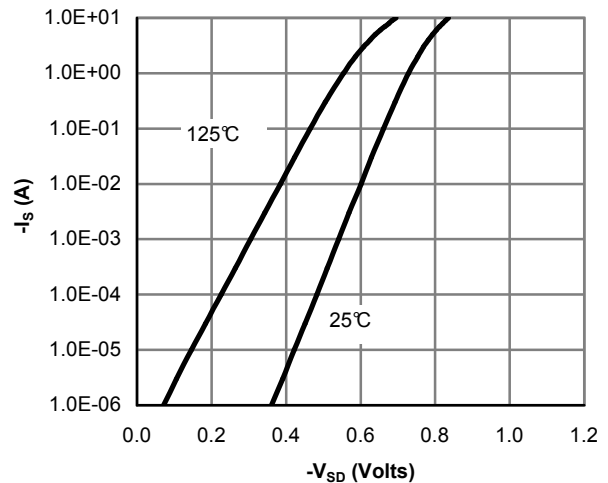


Figure 6: Body-Diode Characteristics

## Dual P-Channel MOSFET AO4815 (KO4815)

■ Typical Characteristics

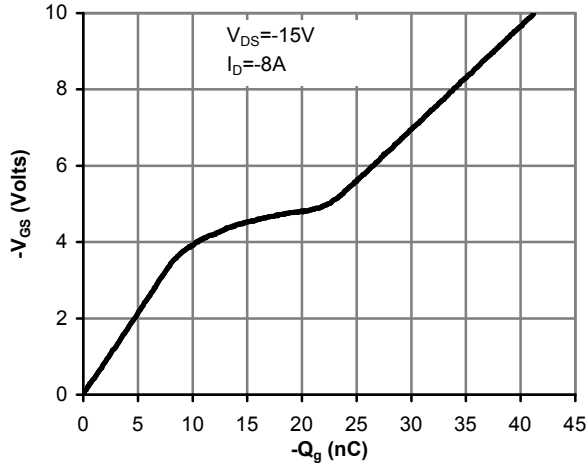


Figure 7: Gate-Charge Characteristics

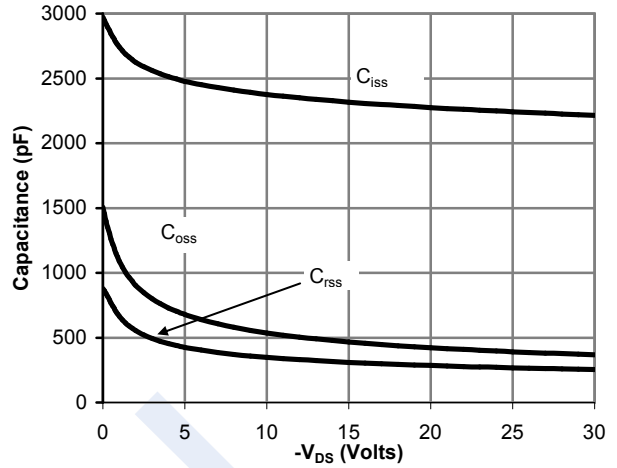


Figure 8: Capacitance Characteristics

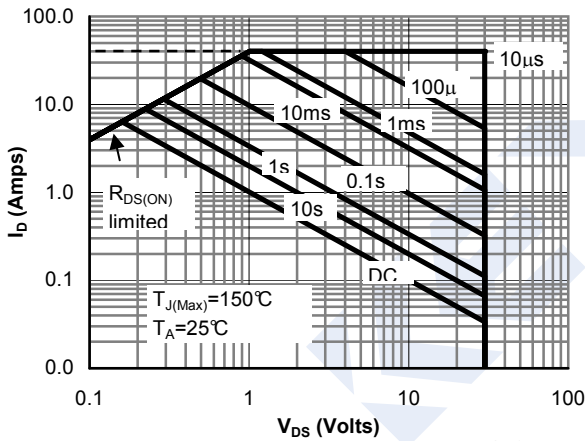


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

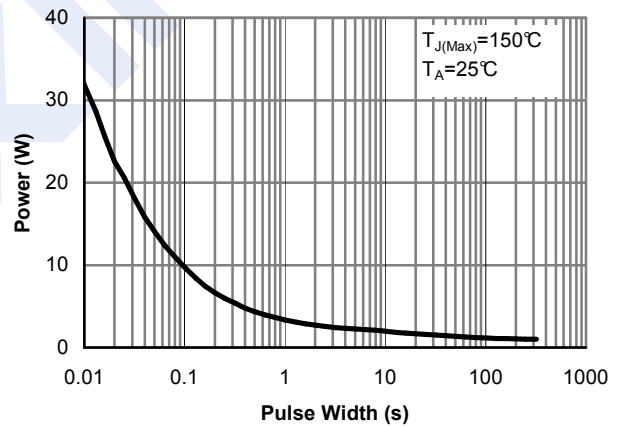


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

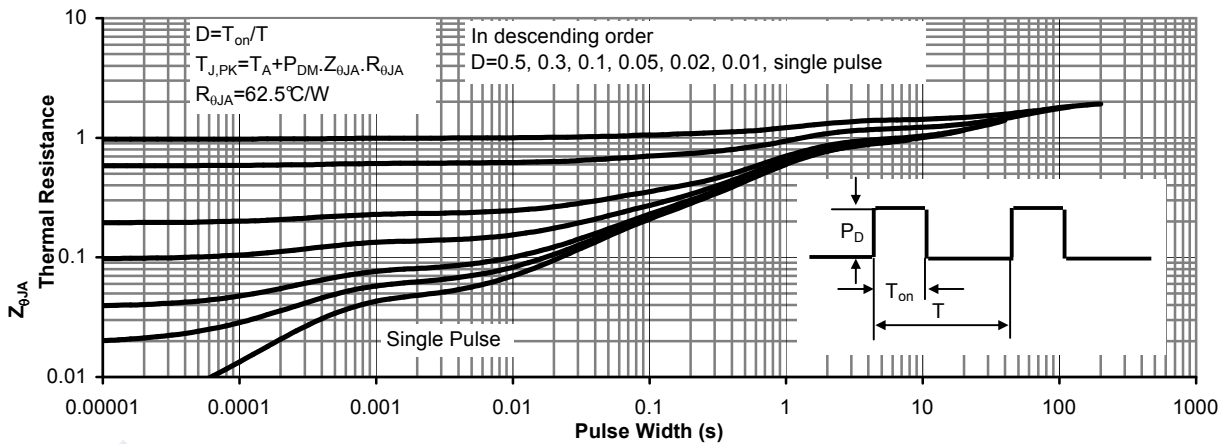


Figure 11: Normalized Maximum Transient Thermal Impedance